

Docket No. 210148US99

IN RE APPLICATION OF: Jamal RAMDANI, et al.

SERIAL NO: 09/885,409

FILED: June 21, 2001

METHOD FOR FABRICATING A SEMICONDUCTOR STRUCTURE INCLUDING A METAL OXIDE INTERFACE WITH SILICON

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Transmitted herewith is an Amendment with Marked-Up Copy in the above-identified application.

- No additional fee is required
- Small entity status of this application under 37 C.F.R. §1.9 and §1.27 is claimed.
- Additional documents filed herewith:

The Fee has been calculated as shown below:

CLAIMS	CLAIMS REMAINING		HIGHEST NUMBER PREVIOUSLY PAID	NO. EXTRA CLAIMS	RATE	CALCULATIONS
TOTAL	11	MINUS	20	0	× \$18 =	\$0.00
INDEPENDENT	6	MINUS	3	3	× \$84 =	\$252.00
		<input type="checkbox"/> MULTIPLE DEPENDENT CLAIMS			+ \$280 =	\$0.00
						\$252.00
		<input type="checkbox"/> Reduction by 50% for filing by Small Entity				\$0.00
		<input type="checkbox"/> Recordation of Assignment			+ \$40 =	\$0.00
						TOTAL
						\$252.00

A check in the amount of \$252.00 is attached.

- Please charge any additional Fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.
- If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time may be charged to Deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.

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DOCKET NO.: 210148US99



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: GROUP ART UNIT: 2818

IN RE APPLICATION OF:

JAMAL RAMDANI ET AL

SERIAL NO.: 09/885,409

: EXAMINER: NGUYEN, D.H.

FILED: JUNE 21, 2001

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FOR: METHOD FOR FABRICATING A SEMICONDUCTOR STRUCTURE  
INCLUDING A METAL OXIDE INTERFACE WITH SILICON

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Responsive to the Official Action dated June 27, 2002, Applicants request  
reconsideration in view of the following amendments and remarks.

IN THE ABSTRACT

Please cancel the present Abstract and substitute therefore the new Abstract attached  
hereto on a separate sheet.

IN THE CLAIMS

Please cancel Claims 1-20.

10/31/2002 PBRITTON 00000003 150030 09885409

01 FC:1251 Please add new Claims 21- 31 as follows:

110.00 CH

--21. A method of fabricating a semiconductor structure comprising:

providing a silicon substrate having a surface;

forming by atomic layer deposition a monocrystalline seed layer on the  
surface of the silicon substrate; and

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01 FC:1201